



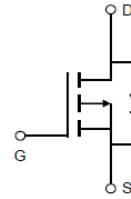
**Product Summary**

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

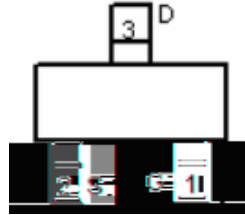


Trench technology

$R_{DS(ON)}$  to minimize conductive loss



Load Switches  
DC/DC



Part NO.	ZM350P02T
Marking	350P02
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

**$T_c = 25$**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current	$I_{D@TC=25}$	-5.1	A
	$I_{D@TC=75}$	-3.8	A
	$I_{D@TC=100}$	-3.2	A
Pulsed Drain Current	$I_{DM}$	-15	A
Total Power Dissipation	$P_D$	1.5	W
Total Power Dissipation( $T_A=25$ )	$P_D@T_A=25$	0.7	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy	$E_{AS}$	25	mJ



Fig.1 Gate-Charge Characteristics

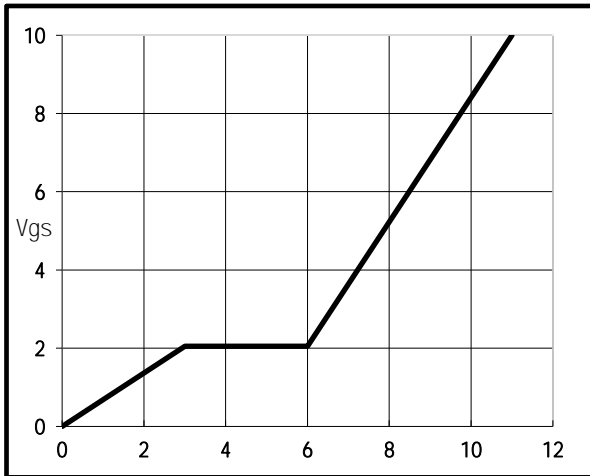


Fig.2 Capacitance Characteristics

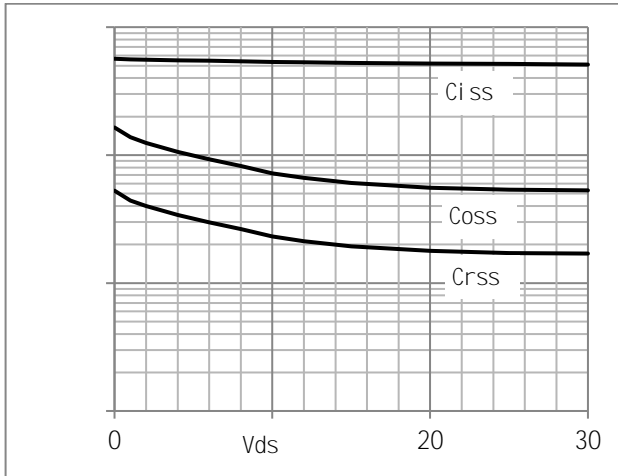


Fig.3 Power Dissipation Derating Curve

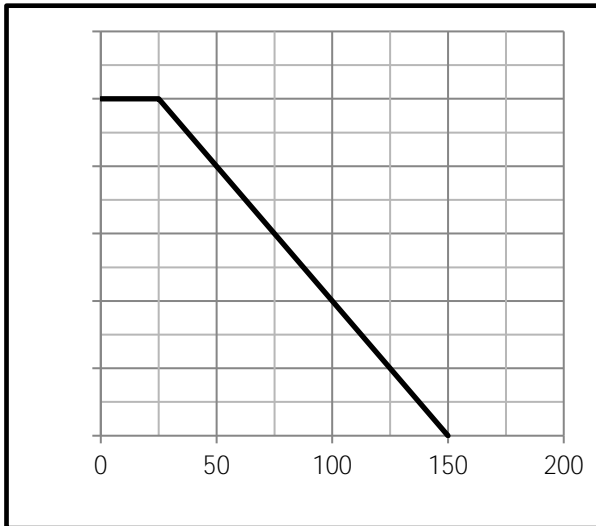


Fig.4 Typical output Characteristics

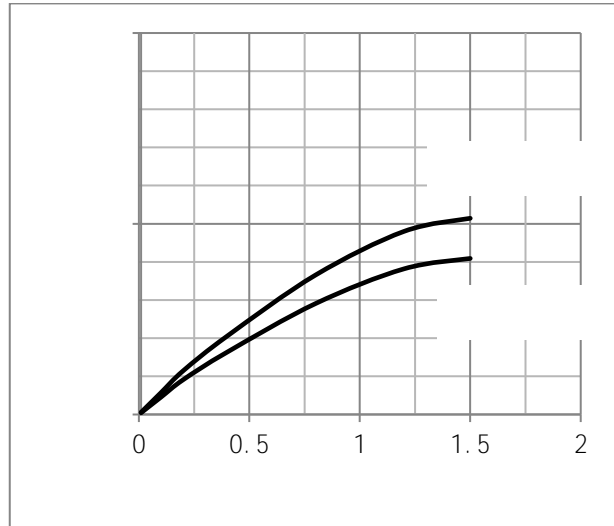


Fig.5 Threshold Voltage V.S Junction Temperature

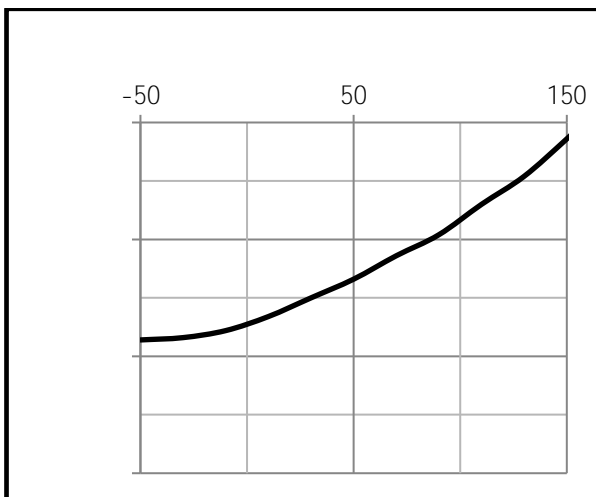
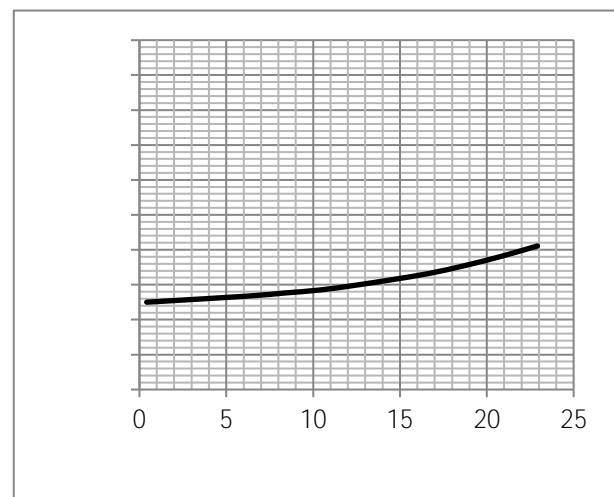


Fig.6 Resistance V.S Drain Current



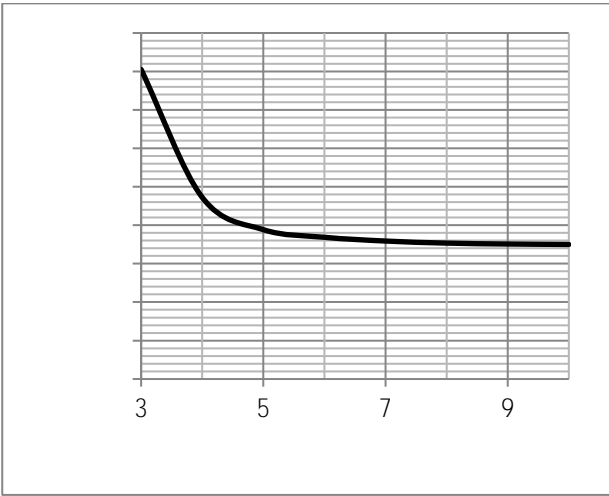


Fig.9 Switching Time Measurement Circuit

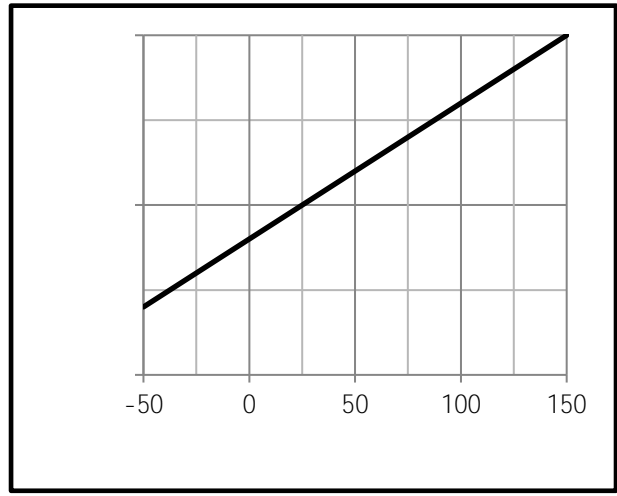


Fig.10 Gate Charge Waveform

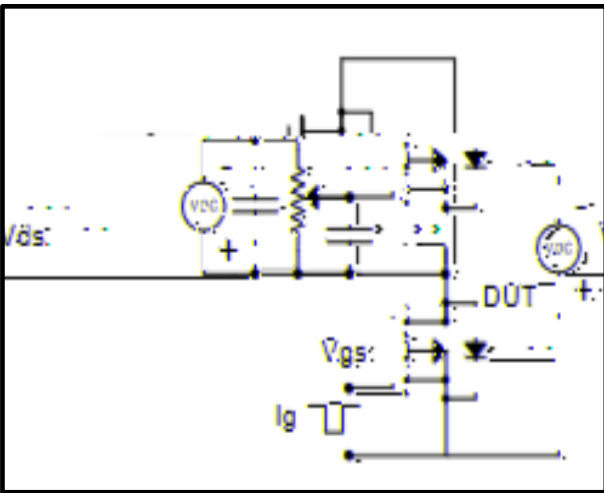


Fig.11 Switching Time Measurement Circuit

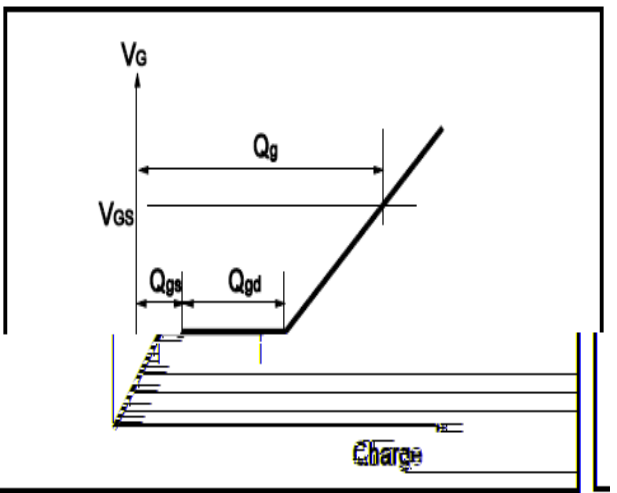


Fig.12 Gate Charge Waveform

